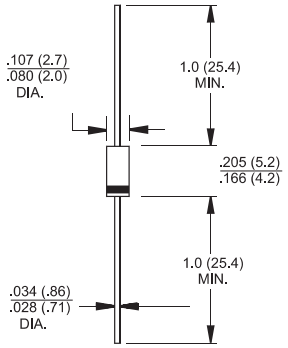
TAIWAN SEMICONDUCTOR

RoHS COMPLIANCE

MUR160A - MUR190A

1.0 AMPS. Glass Passivated High Efficient Rectifiers

DO-41



Dimensions in inches and (millimeters)

Features

- Designed for use in switching power supplies, inverters and as free wheeling diodes
- High efficiency, low VF
- High reliability
- Ultrafast recovery time for high efficiency
- 175°C operating junction temperature
- Green compound with suffix "G" on packing code & marking
- Green compound with suffix "G" on packing code & prefix "G" on datecode.

Mechanical Data

- Cases: Molded plastic
- Epoxy: UL 94V-0 rate flame retardant
- Lead: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
- Polarity: Color band denotes cathode
- High temperature soldering guaranteed: 260°C /10 seconds/.375",(9.5mm) lead lengths at 5 lbs.,(2.3kg) tension
- Weight: 0.34 grams

Marking Diagram

MUR1XX = Specific Device Code
G = Green Compound
Y = Year
WW = Work Week

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%

Type Number	Symbol	MUR160A	MUR190A	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	600	900	V
Maximum RMS Voltage	V_{RMS}	420	630	V
Maximum DC Blocking Voltage	V_{DC}	600	900	V
Maximum Average Forward Rectified Current (Square Wave Note 4) @ T_A=80°C	$I_{(AV)}$	1.0		A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	35		A
Maximum Instantaneous Forward Voltage @ 1.0A Tj=150°C Tj=25°C	V_F	1.05 1.25	1.5 1.7	V
Maximum DC Reverse Current @ T_A=25°C at Rated DC Blocking Voltage @ T_A=125°C	I_R	5.0 150		uA uA
Maximum Reverse Recovery Time (Note 2)	Trr	50	75	nS
Typical Junction Capacitance (Note 1)	Cj	27	15	pF
Typical Thermal Resistance (Note 3)	$R_{\theta JA}$	50		°C/W
Operating Temperature Range	T_J	-65 to +175		°C
Storage Temperature Range	T_{STG}	-65 to +175		°C

Notes:
1. Measured at 1 MHz and Applied Reverse Voltage of 4.0 Volts D.C.
2. Reverse Recovery Test Conditions: I_F=0.5A, I_R=1.0A, I_{RR}=0.25A
3. Thermal Resistance from Junction to Ambient, with units Mounted on P.C. Board with 0.2" x 0.2" Copper Surface.
4. Pulse Test: Pulse Width = 300uS, Duty Cycle ≤2.0%.

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RATINGS AND CHARACTERISTIC CURVES (MUR160A THRU MUR190A)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

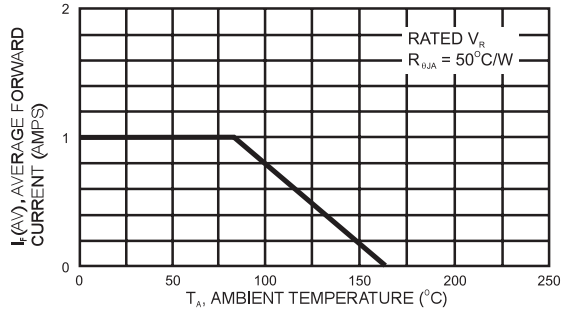


FIG.2- MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

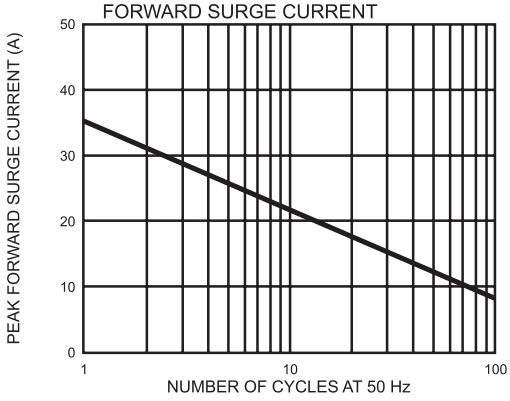


FIG.3- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

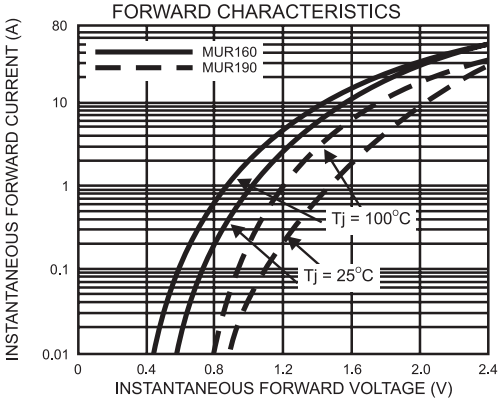


FIG.4- TYPICAL TYPICAL REVERSE LEAKAGE CHARACTERISTICS

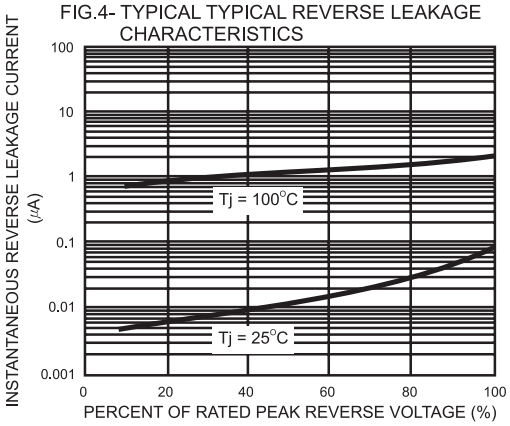


FIG.5- TYPICAL JUNCTION CAPACITANCE

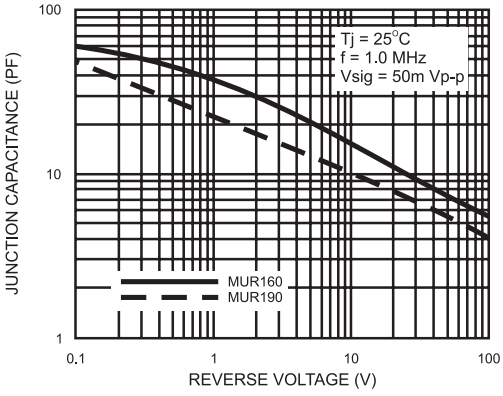
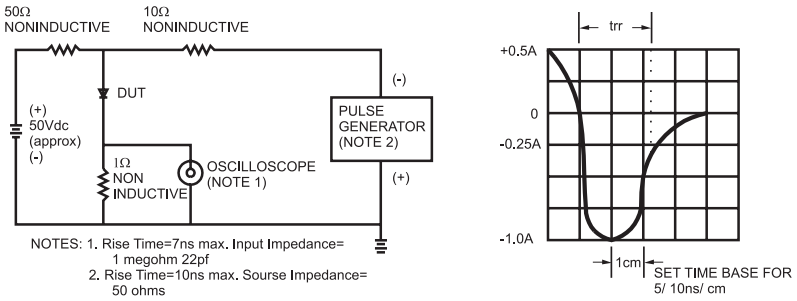


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



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